

METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, SUBSTRATE
PROCESSING METHOD, SUBSTRATE PROCESSING APPARATUS, AND PROGRAM

ABSTRACT

There is provided a technique that includes: (a) nitriding an inner surface of a recessed structure formed on a substrate to modify at least a portion of the inner surface to a nitride layer; and (b) oxidizing the inner surface including the nitride layer to modify the inner surface into an oxide layer. (a) includes setting a thickness distribution of the nitride layer in the inner surface such that a thickness distribution of the oxide layer in the inner surface becomes a desired distribution.

[Representative Drawing]

FIG. 4